



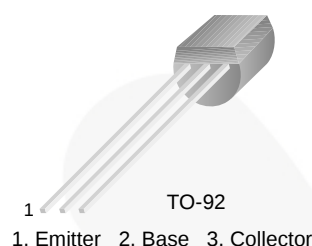
November 2014

SS8050

NPN Epitaxial Silicon Transistor

Features

- 2 W Output Amplifier of Portable Radios in Class B Push-pull Operation.
- Complimentary to SS8550
- Collector Current: $I_C = 1.5\text{ A}$



Ordering Information

Part Number	Top Mark	Package	Packing Method
SS8050BBU	S8050	TO-92 3L	Bulk
SS8050CBU	S8050	TO-92 3L	Bulk
SS8050CTA	S8050	TO-92 3L	Ammo
SS8050DBU	S8050	TO-92 3L	Bulk
SS8050DTA	S8050	TO-92 3L	Ammo

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	1.5	A
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-65 to 150	$^\circ\text{C}$

Thermal Characteristics⁽¹⁾

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	1	W
	Derate Above 25°C	8	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	$^\circ\text{C/W}$

Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 100\ \mu\text{A}$, $I_E = 0$	40			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 2\ \text{mA}$, $I_B = 0$	25			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100\ \mu\text{A}$, $I_C = 0$	6			V
I_{CBO}	Collector Cut-Off Current	$V_{CB} = 35\ \text{V}$, $I_E = 0$			100	nA
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = 6\ \text{V}$, $I_C = 0$			100	nA
h_{FE1}	DC Current Gain	$V_{CE} = 1\ \text{V}$, $I_C = 5\ \text{mA}$	45			
h_{FE2}		$V_{CE} = 1\ \text{V}$, $I_C = 100\ \text{mA}$	85		300	
h_{FE3}		$V_{CE} = 1\ \text{V}$, $I_C = 800\ \text{mA}$	40			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 800\ \text{mA}$, $I_B = 80\ \text{mA}$			0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 800\ \text{mA}$, $I_B = 80\ \text{mA}$			1.2	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 1\ \text{V}$, $I_C = 10\ \text{mA}$			1	V
C_{ob}	Output Capacitance	$V_{CB} = 10\ \text{V}$, $I_E = 0$, $f = 1\ \text{MHz}$		9.0		pF
f_T	Current Gain Bandwidth Product	$V_{CE} = 10\ \text{V}$, $I_C = 50\ \text{mA}$	100			MHz

 h_{FE} Classification

Classification	B	C	D
h_{FE2}	85 ~ 160	120 ~ 200	160 ~ 300

Typical Performance Characteristics

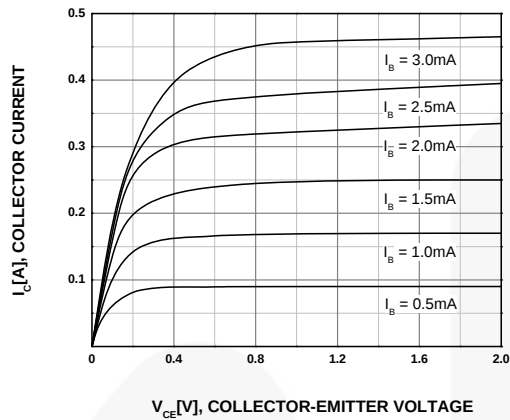


Figure 1. Static Characteristic

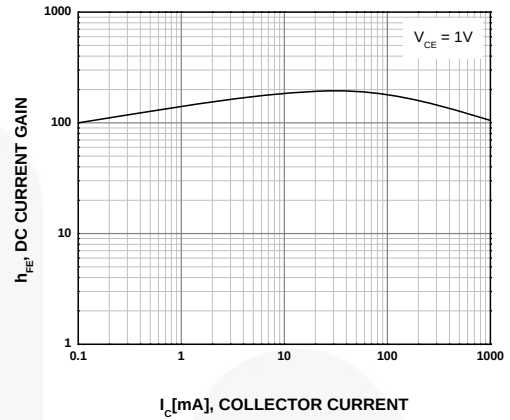


Figure 2. DC Current Gain

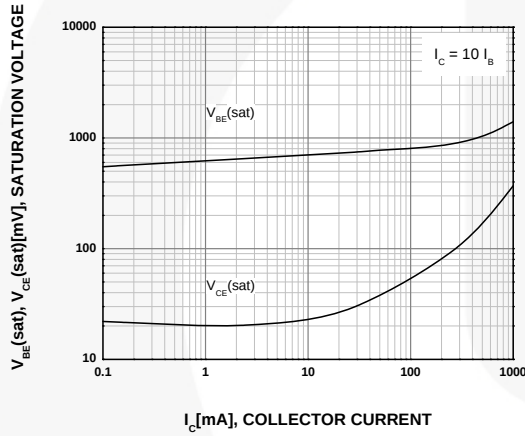


Figure 3. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

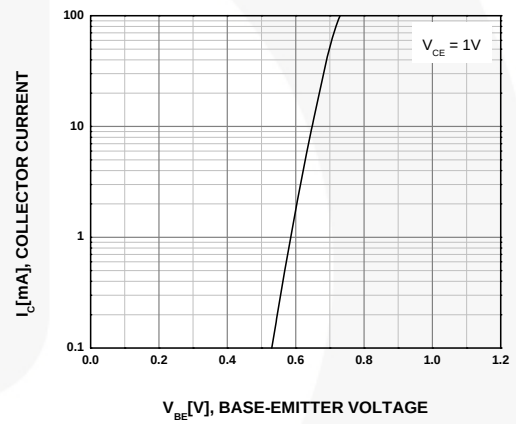


Figure 4. Base-Emitter On Voltage

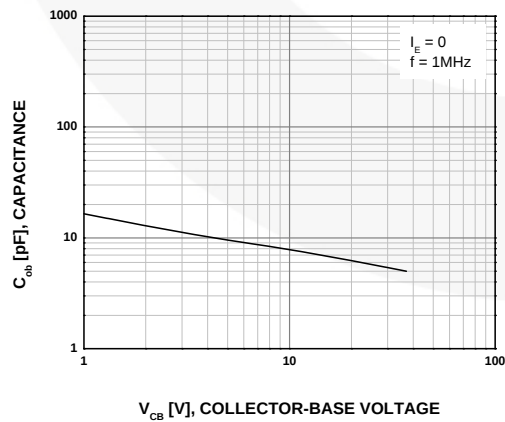


Figure 5. Collector Output Capacitance

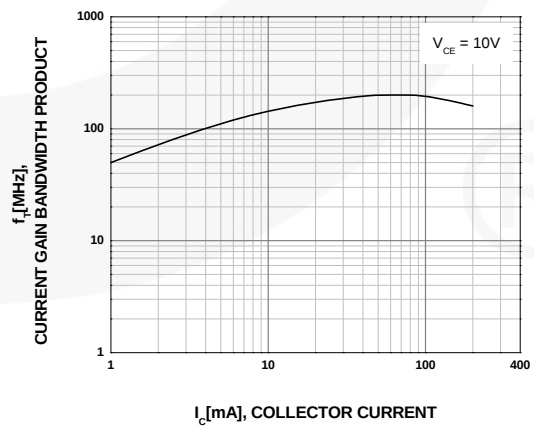
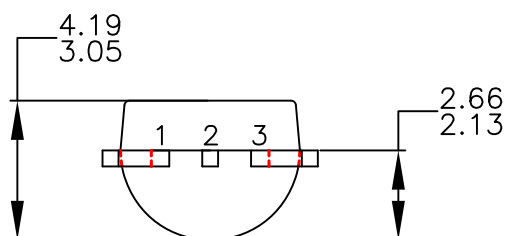
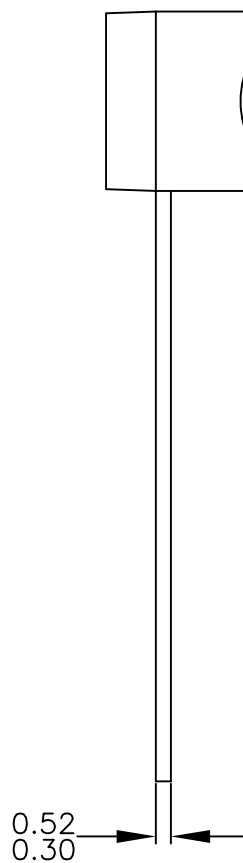
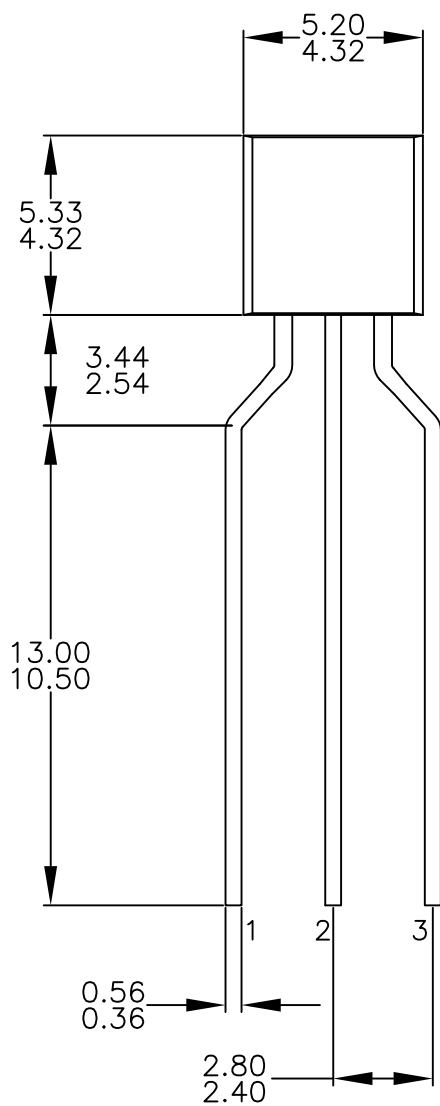


Figure 6. Current Gain Bandwidth Product



NOTES: UNLESS OTHERWISE SPECIFIED

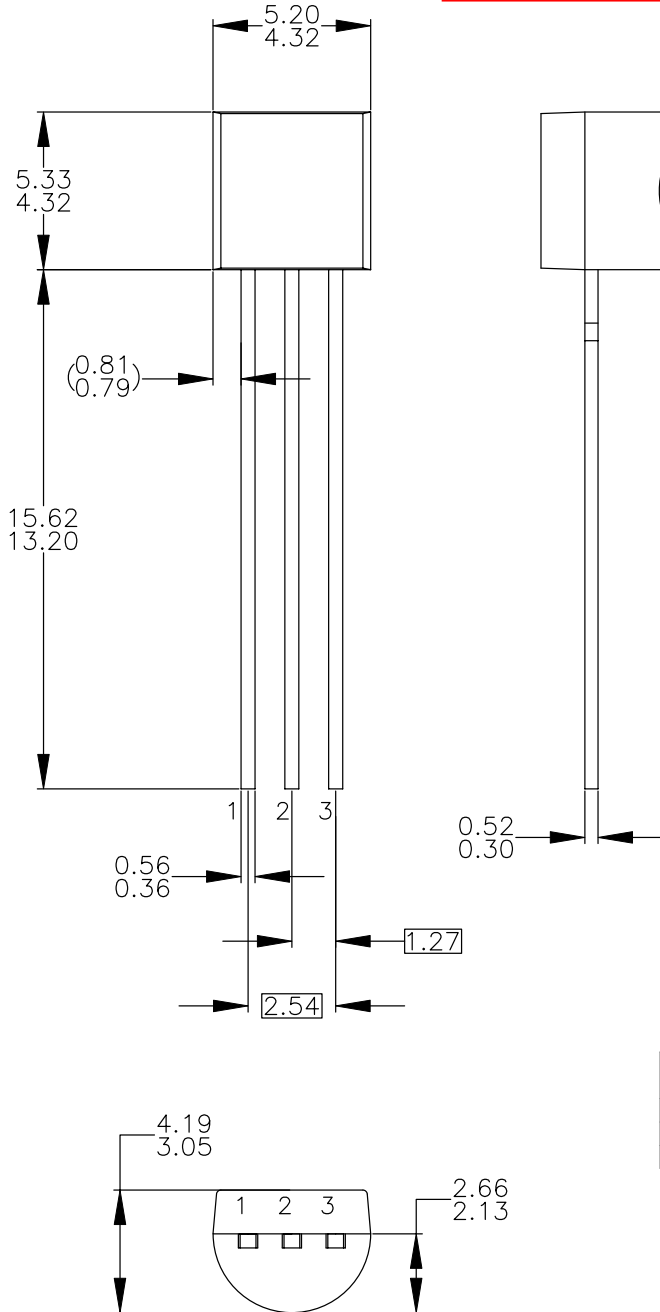
- DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DRAWING CONFORMS TO ASME Y14.5M-2009.
- DRAWING FILENAME: MKT-ZA03FREV3.
- FAIRCHILD SEMICONDUCTOR.

THIS DRAWING IS THE PROPERTY OF FAIRCHILD SEMICONDUCTOR CORPORATION. NO USE THEREOF SHALL BE MADE OTHER THAN AS A REFERENCE FOR PROPORTIONS AS SUBMITTED TO FAIRCHILD SEMICONDUCTOR CORPORATION FOR JOBS TO BE EXECUTED IN CONFORMITY WITH SUCH PROPORTIONS UNLESS THE CONSENT OF SAID FAIRCHILD SEMICONDUCTOR CORPORATION HAS PREVIOUSLY BEEN OBTAINED. NO PART OF THIS DRAWING SHALL BE COPIED OR DUPLICATED OR ITS CONTENTS DISCLOSED. THE INFORMATION CONTAINED ON THIS DRAWING IS CONFIDENTIAL AND PROPRIETARY.

APPROVED
July-14-2008

REVISIONS

NO.	DESCRIPTION	DATE	NAME/SITE
A	RELEASE TO DOCUMENT CONTROL	MAR.4'96	RP
B	RDRW AS PER STD DWG TEMPLATE. CHG DIM REF FR DUAL DIM INCH(MM) TO SINGLE DIM MM. CHG LD PITCH DIM FR 1.14-1.40 TO 1.27 BSC. ADD DIM 2.54 BSC. CHG PKG WIDTH DIM FR 4.32- 4.70 TO 4.32-4.83; CHG PKG HEIGHT DIM FR 4.32-4.70 TO 4.32-4.78; CHG LD THICK DIM FR 0.30- 0.48 TO 0.30-0.52; DAMBAR-PKG DIM FR 1.27-1.65 TO 0.90-1.65; LD LGH DIM FR 14.47-15.64 TO 14.47-15.62; PKG DIM: 1.02-1.52 TO 0.92-1.52, 3.61-4.45 TO 3.40-4.80; NOTE 2: ADD DMOS "M" OPT'N AND LEGEND; NOTE B PKG 94 JFET OPT'N: CHG D TO S, CHG S TO D. ADD NOTE C; MOVE NOTE B INFO FR PKG 97&98 TO NEW NOTE D.	4OCT1999	RCM/MRG
3	CHG LD LEN FR 15.62 TO 15.62; CHG MOLD BODY HT FR 4.32 TO 4.32; CHG PKG EDGE TO LD EDGE DIST FR (0.81) TO (0.81); CHG MOLD BODY WIDTH FR 1.27 TO 1.27; ADD PKG THICKNESS DIM "E"; CHG "S" DIM FR 2.13 TO 2.13; REMOVE DAMBAR & EJECTOR PIN LOCATOR FEATURES & DIMENSIONS; REMOVE MOLDED SURFACE & DRAFT ANGLE DIMS; ADD NOTE ON JEDEC REFERENCE; ADD NOTE ON ASME Y14.5M-1994; REMOVE NOTE ON L34Z OPTION; ADD NOTE ON DWG FILENAME.	12FEB08	BMR/FSCP



NOTES: UNLESS OTHERWISE SPECIFIED

- DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DRAWING CONFORMS TO ASME Y14.5M-1994.
- TO-92 (92,94,96,97,98) PIN CONFIGURATION:

PIN	92	94	96	97	98
1	E S S	E S S	B D G	C G D	C G D
2	B D G	C G D	E S S	B D G	E S S
3	C G D	B D G	C G D	E S S	B D G

LEGEND:

P - BIPOLAR E - EMITTER D - DRAIN
F - JFET B - BASE S - SOURCE
M - DMOS C - COLLECTOR G - GATE

- FOR PACKAGE 92, 94, 96, 97 AND 98:
PIN CONFIGURATION DRAIN "D" AND SOURCE "S"
ARE INTERCHANGEABLE AT JFET "F" OPTION.
- DRAWING FILENAME: MKT-ZA03DREV3.

APPROVALS	DATE	FAIRCHILD SEMICONDUCTOR™ 3LD, TO-92, MOLDED STD STRAIGHT LD (NO EOL CODE)	SCALE	SIZE	DRAWING NUMBER	REV
DRAWN: J.U. COMPARATIVO JR.	03APR2008		1:1	N/A	MKT-ZA03D	3
CHECKED: L. GALERA			FORMERLY: N/A			
APPROVED: M.R. GESTOLE			SHEET : 1 OF 1			
G.S. BAJE						



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™	F-PFS™	OPTOPLANAR®	SYSTEM GENERAL®*
Awinda®	FRFET®		TinyBoost®
AX-CAP®*	Global Power Resource™	PowerTrench®	TinyBuck®
BitSiC™	GreenBridge™	PowerXS™	TinyCalc™
Build it Now™	Green FPS™	Programmable Active Droop™	TinyLogic®
CorePLUS™	Green FPS™ e-Series™	QFET®	TINYOPTO™
CorePOWER™	Gmax™	QS™	TinyPower™
CROSSVOLT™	GTO™	Quiet Series™	TinyPWM™
CTL™	IntelliMAX™	RapidConfigure™	TinyWire™
Current Transfer Logic™	ISOPLANAR™		TranSiC™
DEUXPEED®	Making Small Speakers Sound Louder and Better™	Saving our world, 1mW/W/kW at a time™	TriFault Detect™
Dual Cool™	MegaBuck™	SignalWise™	TRUECURRENT®*
EcoSPARK®	MICROCOUPLER™	SmartMax™	μSerDes™
EfficientMax™	MicroFET™	SMART START™	
ESBC™	MicroPak™	Solutions for Your Success™	UHC®
	MicroPak2™	SPM®	Ultra FRFET™
Fairchild®	MillerDrive™	STEALTH™	UniFET™
Fairchild Semiconductor®	MotionMax™	SuperFET®	VCX™
FACT Quiet Series™	MotionGrid®	SuperSOT™-3	VisualMax™
FACT®	MTi®	SuperSOT™-6	VoltagePlus™
FAST®	MTx®	SuperSOT™-8	XS™
FastvCore™	MVN®	SupreMOS®	Xsens™
FETBench™	mWSaver®	SyncFET™	仙童™
FPS™	OptoHit™	Sync-Lock™	
	OPTOLOGIC®		

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT [HTTP://WWW.FAIRCHILDSEMI.COM](http://www.fairchildsemi.com). FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I72